



Who am I?

- Kevin Tran
- Senior Manager Technical Marketing



- HBM Product and Ecosystem Champion
- DRAM Memory Solutions for Automotive, Infrastructure and Networking.
- Emerging Memory Technologies



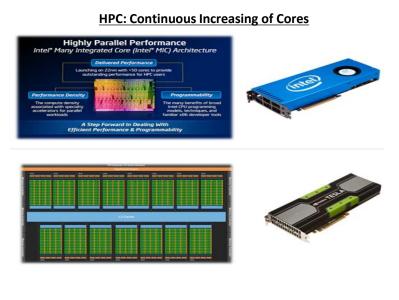
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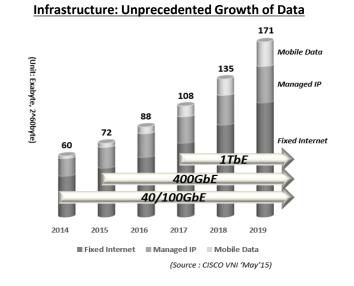
- **1.** Trends driving TSV based DRAM devices
- 2. HBM Overview
- 3. Test/Quality/Reliability
- 4. Next-generation TSV Solutions



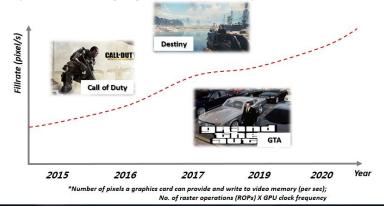
Major Trends Driving Higher Memory Performance

Scaling of DRAM memory density, bandwidth and form factor are critical for next generation processing architectures





Graphics: Increasing High Performance Graphics Card Max. Fillrate



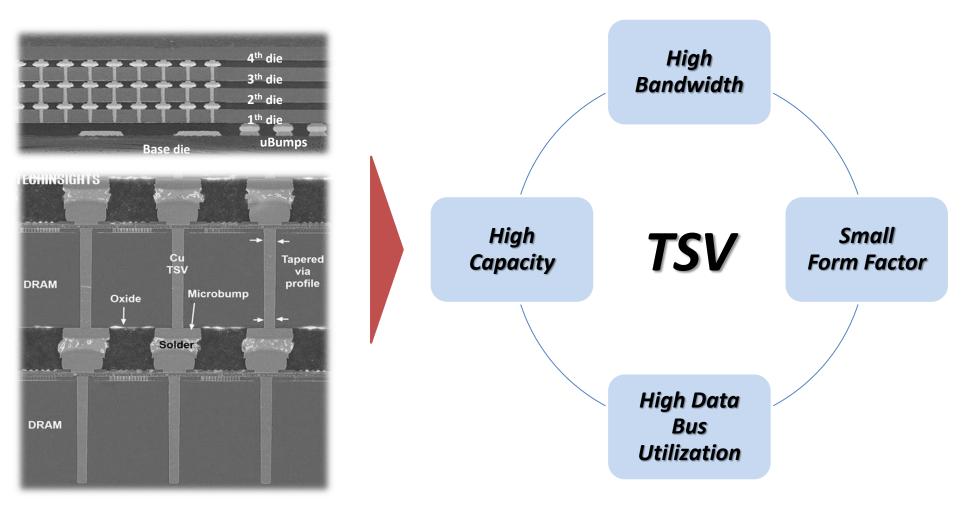
Network: Ethernet Speed Demands Scaling of Memory Bandwidth

	Ethernet Interface						
	10GbE	25GbE	40GbE	100GbE	400GbE	1TbE	
Speed*	30Gbps	75Gbps	120Gbps	300Gbps	1.2Tbps	3Tbps	

*Speed = Read/Write x Overhead 150% x Ethernet Interface



Through Silicon Via (TSV) technology enable DRAM memory to overcome existing performance challenges



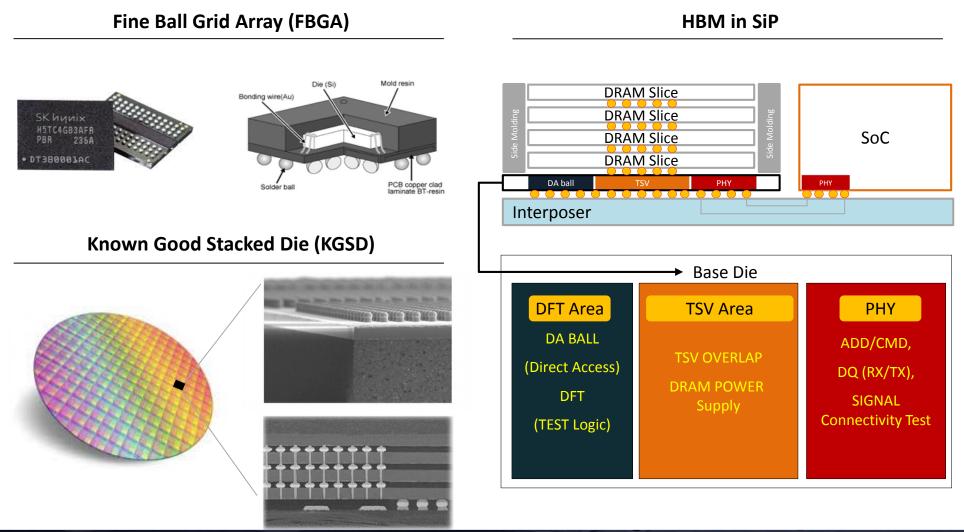




2. High Bandwidth Memory Overview



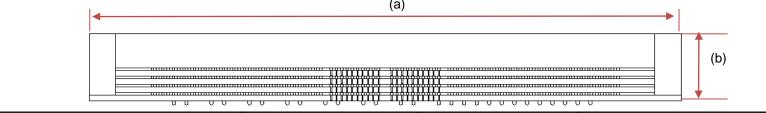
Known Good Stacked Die(KGSD) DRAM Memory for 2.5D System in Package integration



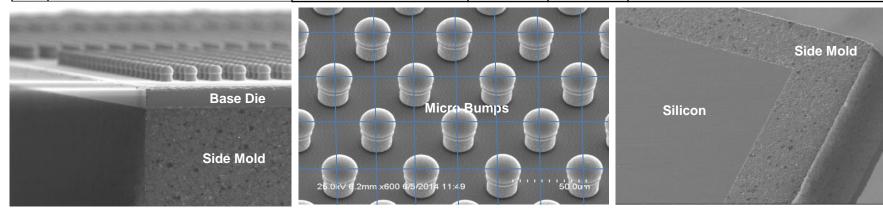




• mKGSD (1 Base + 2/4/8 DRAM (Core) ; molded Known Good Stacked Die)



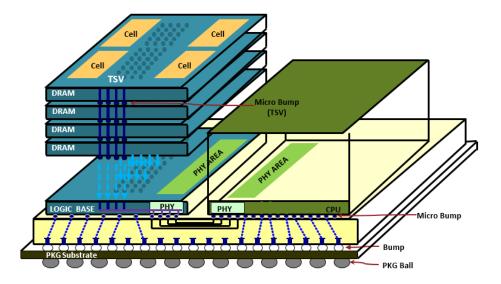
	ltem	Value Bump		mp	Remark	
	item	value	CD	Pitch	Remark	
(a)	Gen1 - Package Dimension (X, Y)	5.48 mm x 7.29mm			Face Centered Rectangular (FCR) pattern ubump	
	Gen2 - Package Dimension (X, Y)	7.75 mm x 11.87mm	25um	55um	FCR	
(b)	Gen1 - Package Body Height (Z)	0.49 mm	(As Reflow)			
(b)	Gen2 - Package Body Height (Z)	0.72 mm				
	Micro Bump Array (MPGA)	JEDEC	-	-	JC11-2.883, JC11-4.884	







HBM 1024 IO from base die PHY region connect to host PHY through the interposer



Features	Spec		
Burst Length	2, 4		
# of Die per Stack	2/4/8 DRAM (+1 Base Die)		
Density per Stack	2GB 4GB 8GB avail		
Channels / Stack	8		
Channel / DRAM Slice	Up to 8 (2/4)		
Banks / Channel	8/16		
IO / Channel	128		
Prefetch / Channel	32B (128x2bit)		
Total Data IO Width	1024		
Logic Buffer Data IO / Rate	1024 DQ's @ 1GT (500MHz)		
Peak Read BW / Stack	Up to 256GB/s		
Page Size	2КВ		
DRAM Core voltage	1.2V		
Logic Buffer IO voltage	1.2V		

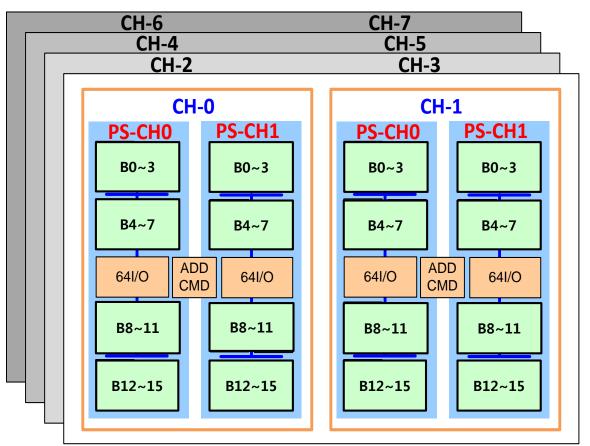




Each DRAM core die consists of a number of Channels

Pseudo Channel Mode - separate IO but independent ADD/CMD for each pseudo-

channel



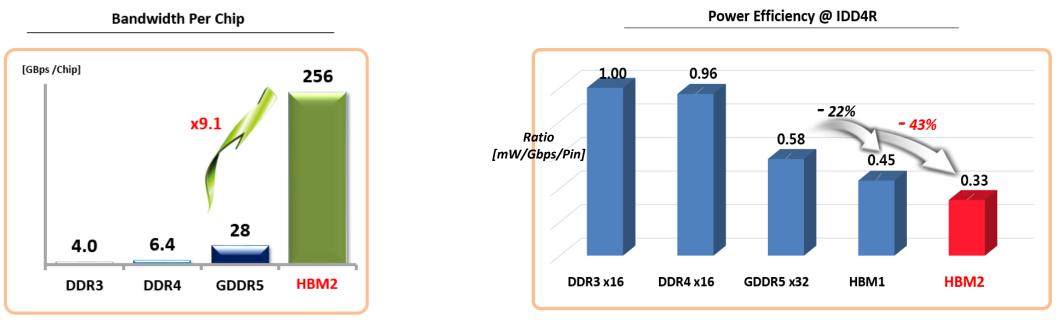
Note: this is an illustration of a design with 2 Channels per DRAM slice



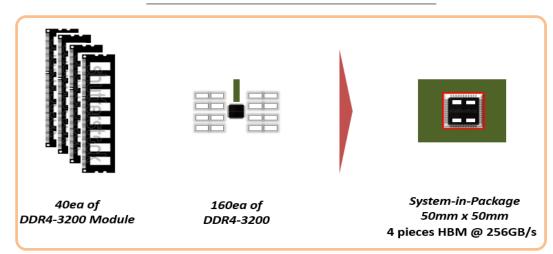


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HBM Advantages



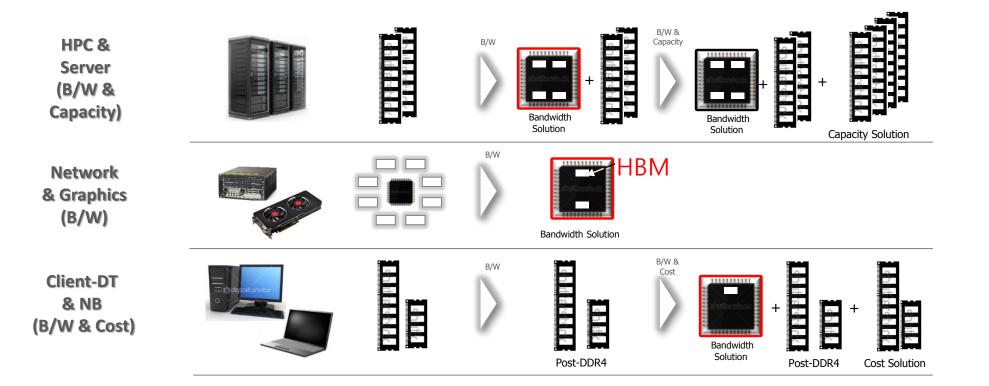
To Achieve 1TB Bandwidth





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HBM is designed to address multiple needs of next generation systems







Different HBM2 line-ups available for different needs of various market segments

8Gb/4Gb based	9mKGSD(8 Hi)			5	mKGSD(4 F	li)	3mKGSD(2 Hi)		li)
Density/Cube(GB)	8				4		2		
IO(DQ)	1024				1024		1024		
Speed/Pin(Gb/s)	1.0	1.6	2.0	1.0	1.6	2.0	1.0	1.6	2.0
Bandwidth(GB/s)	128	204	256	128	204	256	128	204	256
Usage	HPC, Server, Network		HPC,	Server, Gra Network	phics,	Graphics, Cache		he	
Configuration	HBM			HBM HBM		HBM			

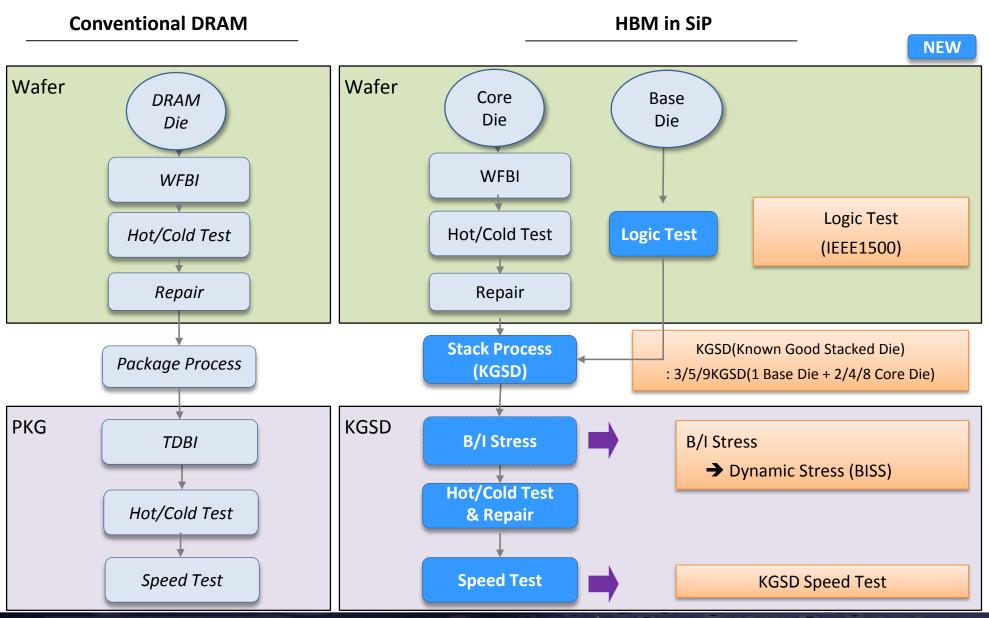




3. High Bandwidth Memory – Test/Quality/Reliability



HBM Test Flow

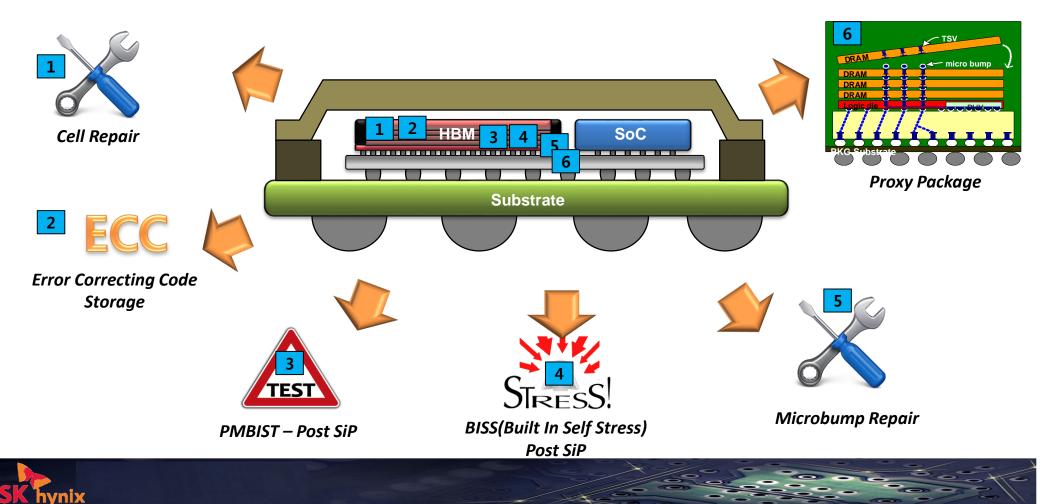




SK hynix

vniv

HBM features enable high quality and reliability at post 2.5D assembly

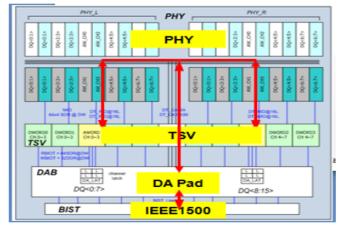


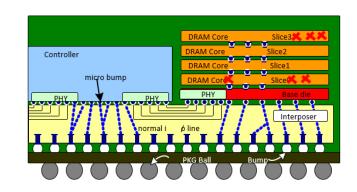


Post Package Repair – DRAM Cells & TSV/ubumps

HBM includes test/repair features for Post SiP assembly through IEEE1500 standards HBM provides Soft & Hard Post Package Repair (PPR) functions

KGSD (Base/Core)

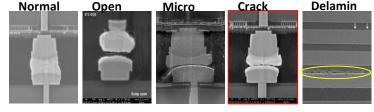


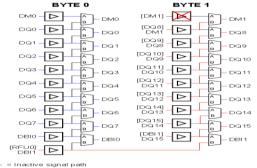


Test Area	Function	Detail item	Coverage
РНҮ	Function Test RD/WT,CL,BL		100%
PHY	Margin Test	Speed, VDD, Setup/Hold Timing	100%
TCV	Function Test RD/WT,CL,BL,TSV interface		100%
TSV	OS Check	TSV Open/Short Check	100%
Logic	Function Test	IEEE1500, Function, BIST, Repair	100%
	Margin Test	VDD, Speed, Setup/Hold	100%
	Function Test	nction Test RD/WT, Self Ref, Power Down	
Core	Margin Test Speed, VDD, Async, Refresh		100%
	Repair	Cell Repair	100%

MBIST enable DRAM Cell Test and Repair through IEEE1500

- Conducted after SiP Assembly
- 4-Row Rep / 2-Bank (Repair DRAM)
- (64 row per channel @ 8Hi)
- Performed via MBIST





HBM supports interconnect lane remapping through

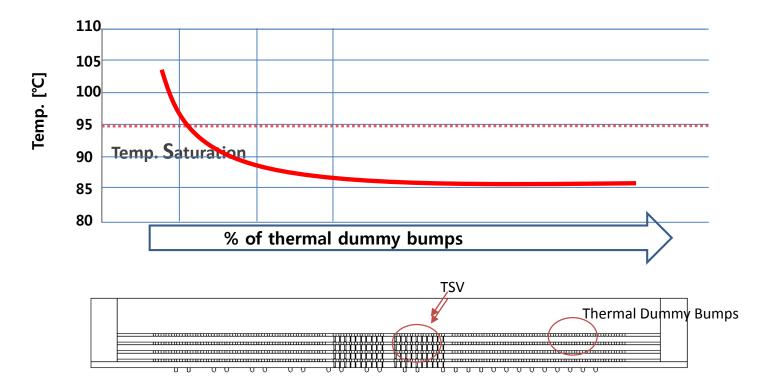
IEEE1500 instructions

- Conducted after SiP Assembly
- Lane remapping is independent for each channel





- Thermal dummy bumps enhance thermal dissipation
- There are no mechanical reliability issues by thermal dummy bumps







Item	Remarks
	Datasheet (Jedec / Vendor)
Euroctionality	Verilog (Mission mode & DFT)
Functionality	IBIS
	Hspice
	GDS
Mechanical/Interposer Design	Bump pad netlist
	Bump ballout
Thermal Simulation	Flotherm
	Icepak

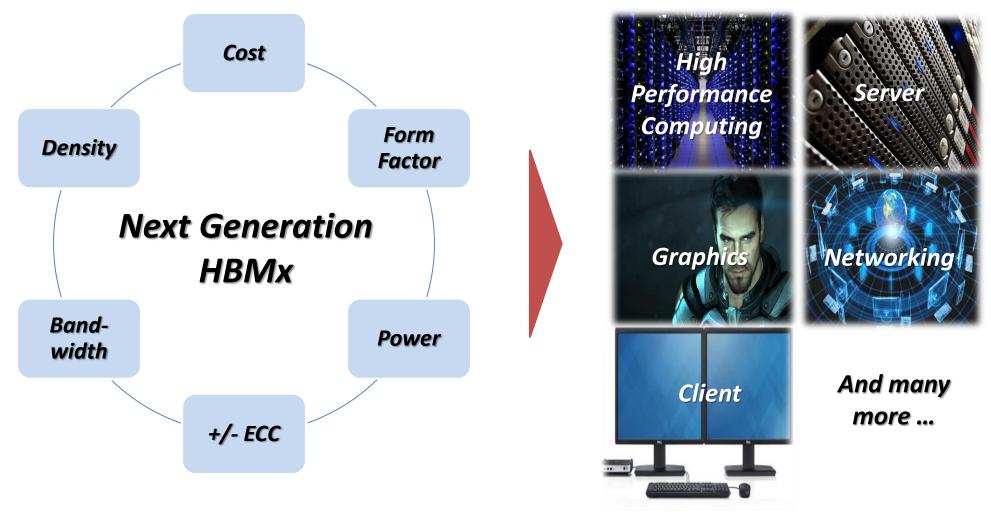


5. Future TSV based DRAM solutions



5. Next Generation TSV Solutions

Next generation HBMx will target multiple applications





Conclusion

- HBM is a breakthrough memory solution for performance, power and form-factor constrained systems by delivering high bandwidth, Low effective power & Small form factor
- HBM device provide various mechanisms to ensure quality/reliability at pre and post SiP assembly
- HBM is an industry standard solution with multiple supply sources

Thank You!



